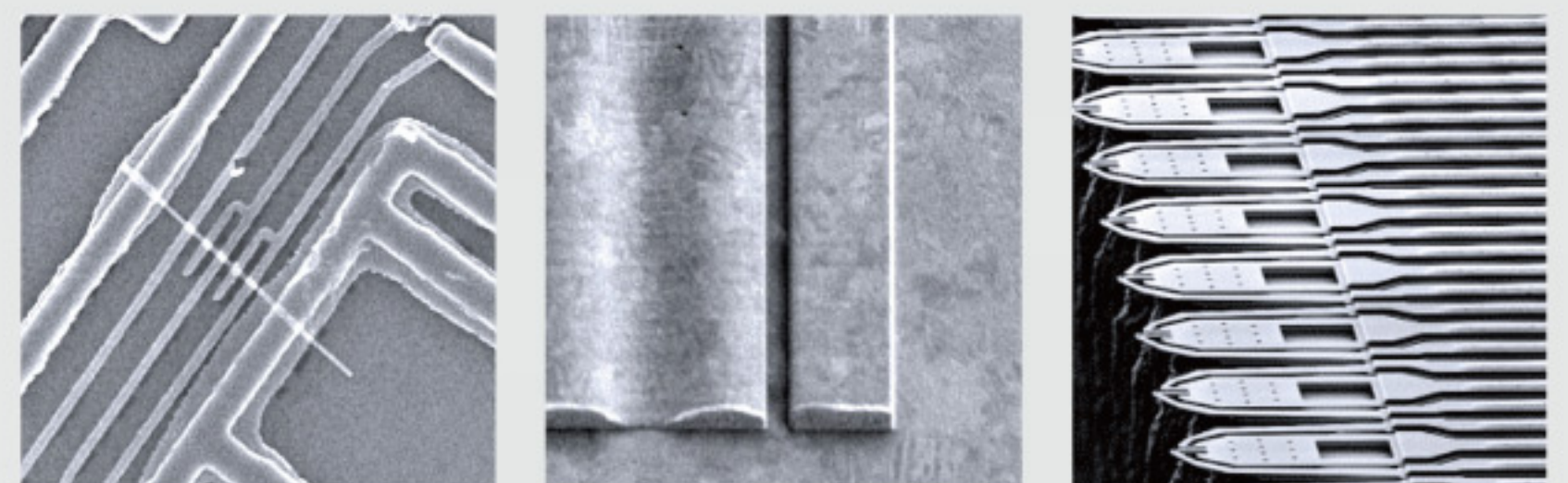


NanoFrazor[®] Explore

REVOLUTIONIZING NANOFABRICATION

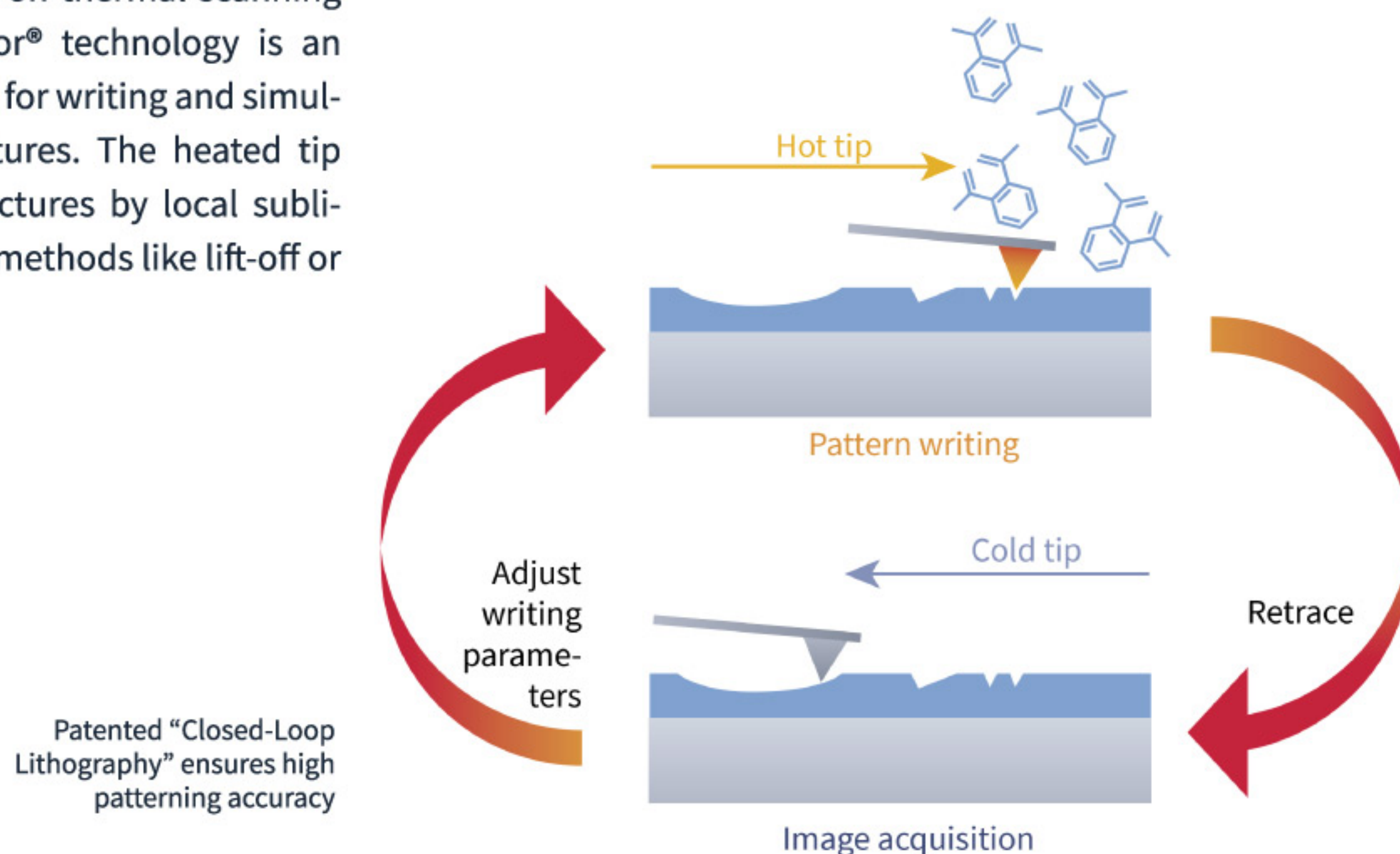


NanoFrazor[®] Explore

THE FIRST HYBRID MIX&MATCH NANO- AND MICROLITHOGRAPHY TOOL

The NanoFrazor[®] Explore takes nanofabrication to a new level. The NanoFrazor technology has been commercially available since 2014, and its unique capabilities have already enabled many revolutionary nanotechnology devices and discoveries.

NanoFrazor lithography systems are based on thermal scanning probe lithography. Core of the NanoFrazor[®] technology is an ultra-sharp heatable probe tip which is used for writing and simultaneous inspection of complex nanostructures. The heated tip creates arbitrary, high-resolution nanostructures by local sublimation of resists. Standard pattern transfer methods like lift-off or etching can be applied.



PPA - THE MAIN RESIST FOR NANOFRAZOR TECHNOLOGY

- Polyphthalaldehyde (PPA) decomposes and sublimates without redeposition upon heating by tip or laser
- PPA is suitable for many pattern transfer processes (lift-off, etching, molding, ...). We provide support and an extensive recipe book.
- PPA is commercially available worldwide
- Contact us for info on other resists and transfer processes

HYBRID MIX & MATCH DIRECT WRITE LITHOGRAPHY

Since 2019, the NanoFrazor[®] Explore is also equipped with a laser writer module. The increased write speed at micrometer resolution makes the Explore the first real alternative to expensive and complex direct-write nanolithography methods.

Laser writing

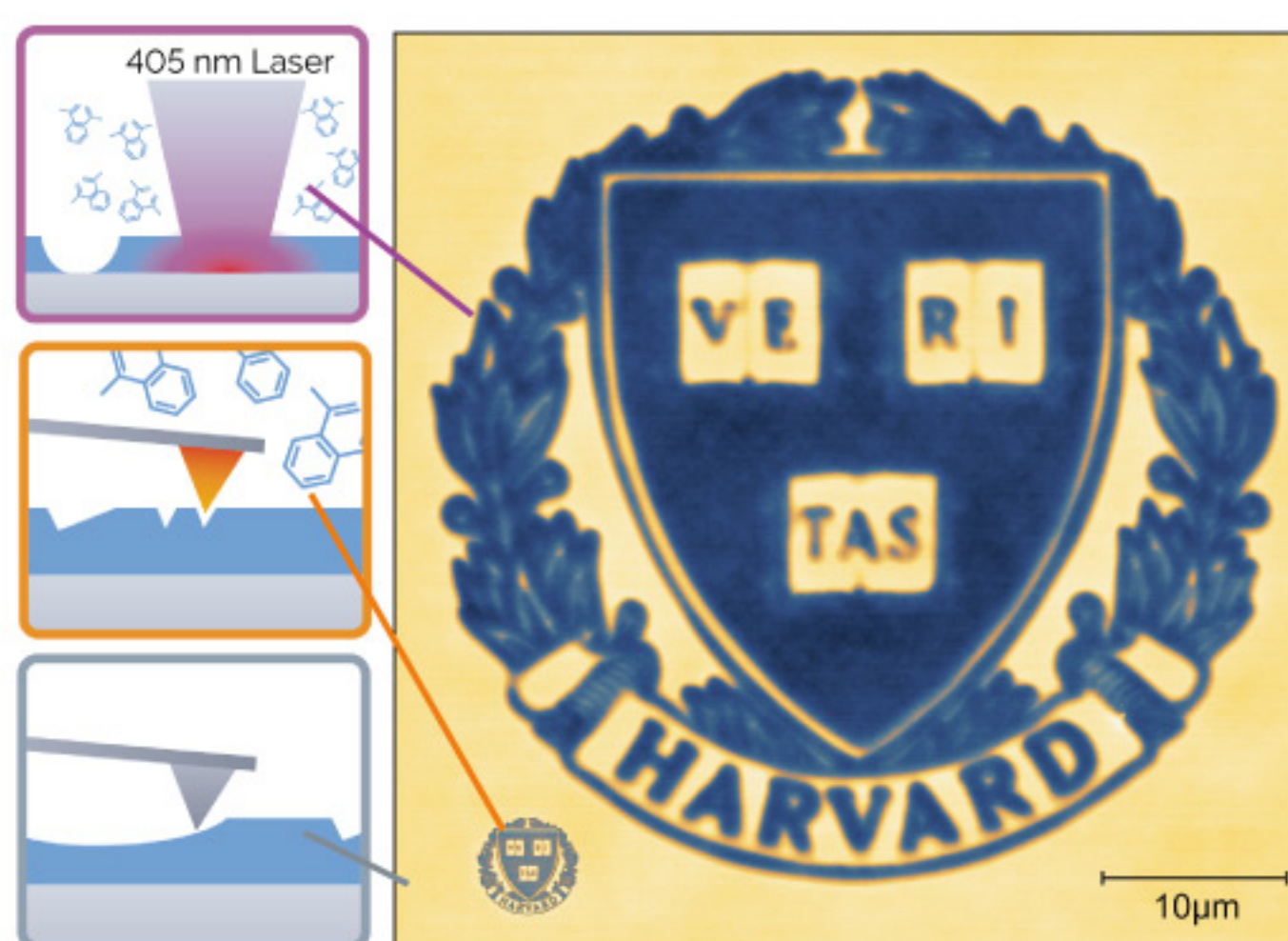
Fast direct resist sublimation for large-area patterning, e.g. contact wires and pads

Thermal probe writing

High precision and high resolution for the critical parts of the nanodevice

Metrology, inspection and alignment

In-situ high-speed imaging with the same tip before, during or after patterning. No wet development required as the PPA resist is removed directly.

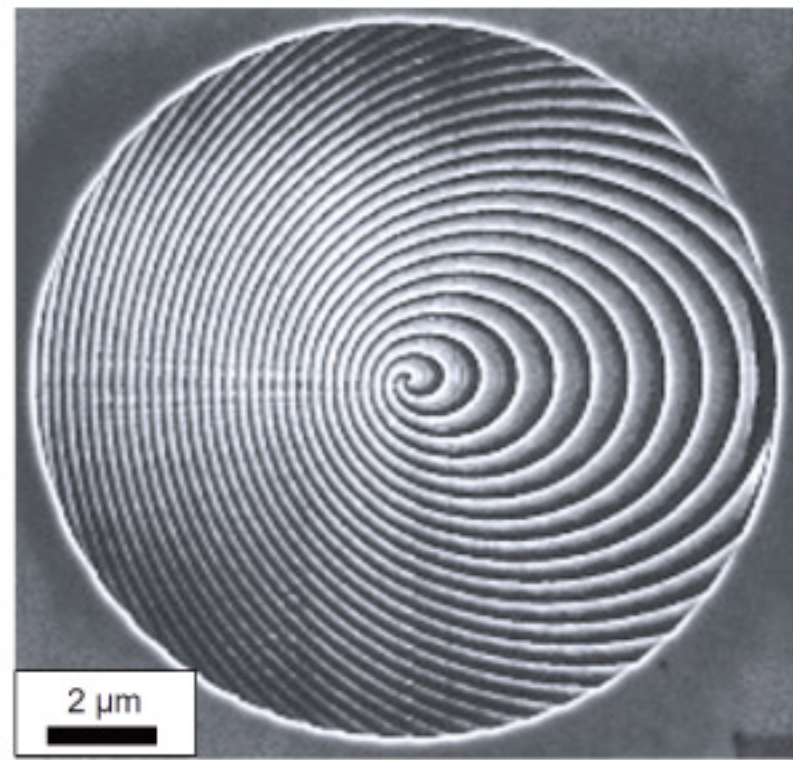


Harvard micro- and nano-logos written 30 nm deep into PPA resist and imaged by NanoFrazor[®]

Courtesy of Harvard CNS

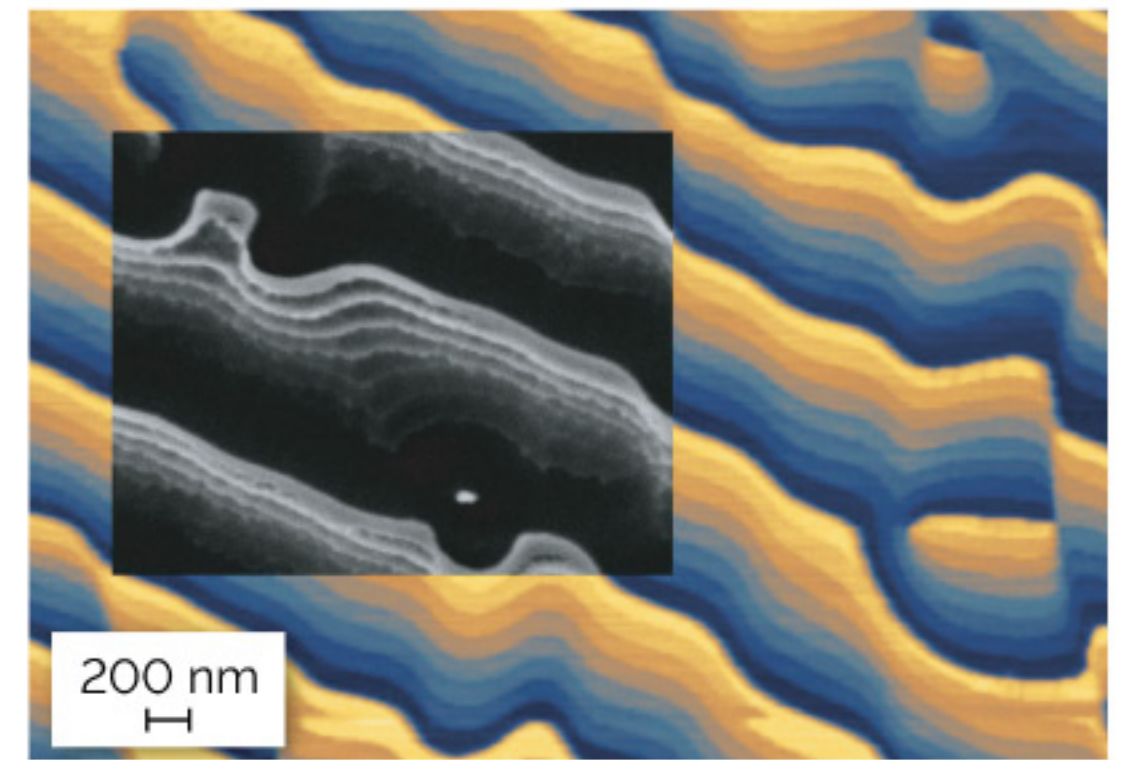
3D GRAYSCALE NANOLITHOGRAPHY

- Patterning depth can be set for each position of the tip (grayscale value of each pixel)
- Closed-Loop Lithography enables unprecedented accuracy (< 1 nm error demonstrated for more than 16 individual depth levels)



3D phase plate etched from PPA into SiN membranes for TEM optics

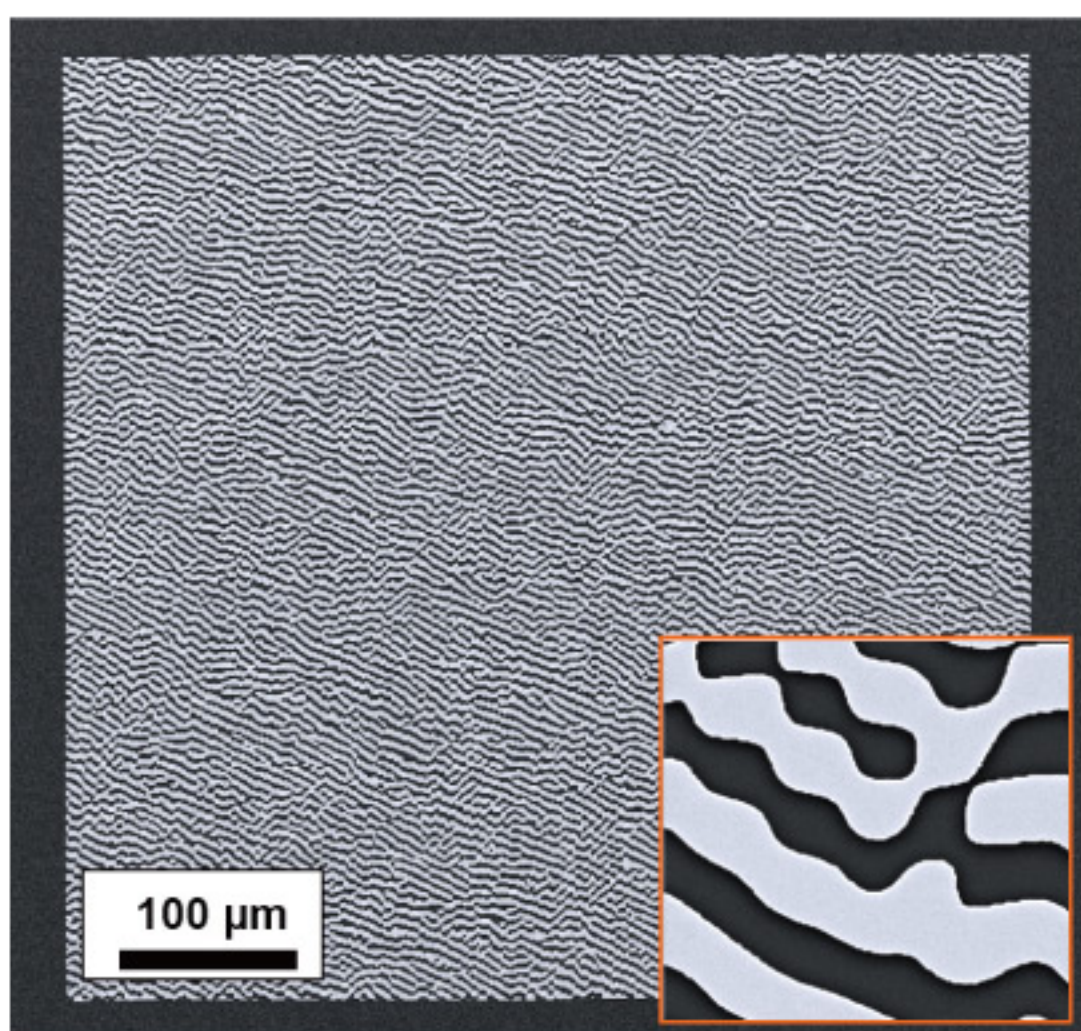
Courtesy of EPFL and KIT



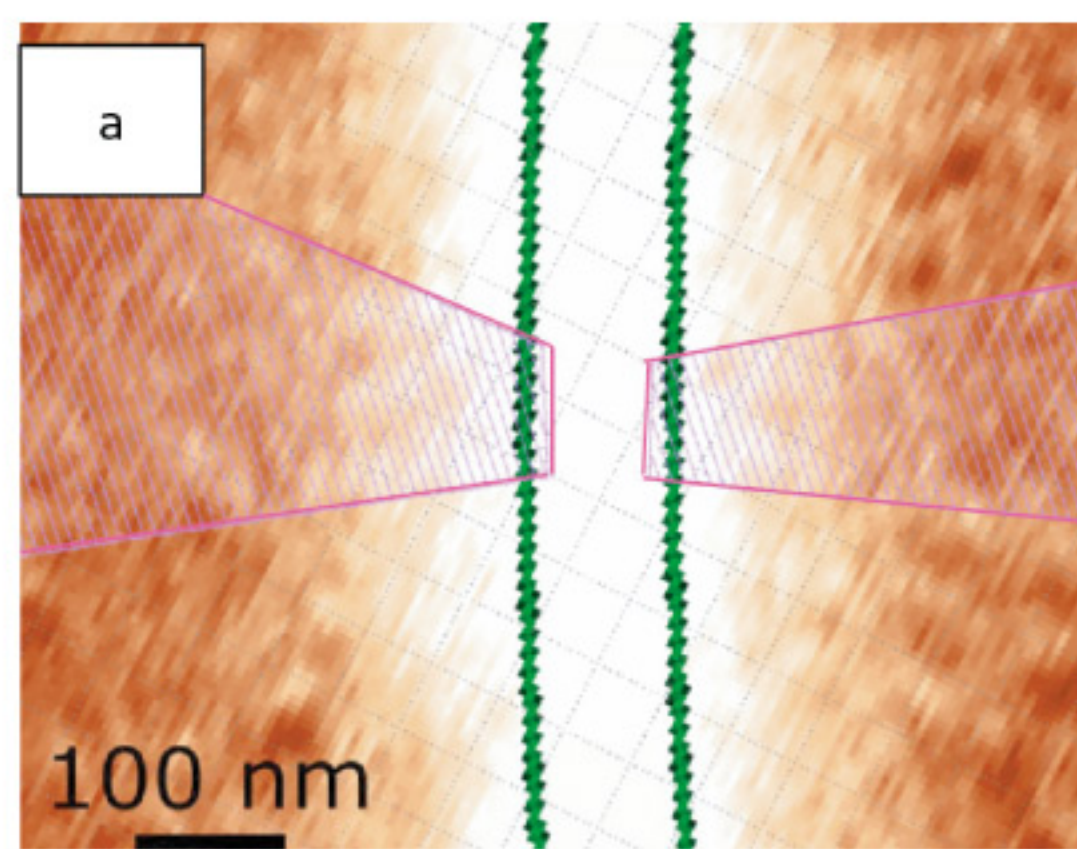
Multilevel hologram written into PPA and simultaneously imaged. Inset is an SEM image after 10x-amplification etch transfer in Si

Courtesy of Sun Yat-Sen University

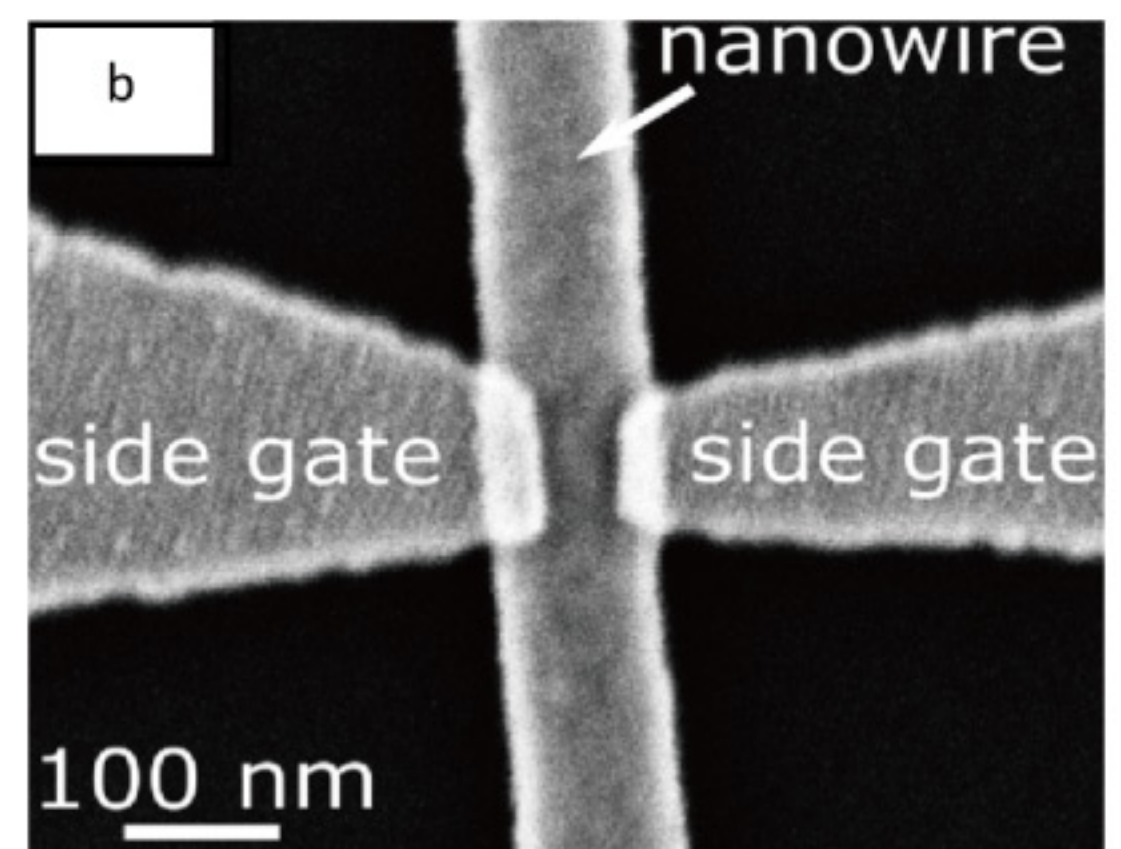
MARKERLESS OVERLAY & STITCHING



Reflective hologram (made with Au lift-off) consisting of 100 000 000 pixels and stitched from 50 μm write fields using a topography correlation technique.

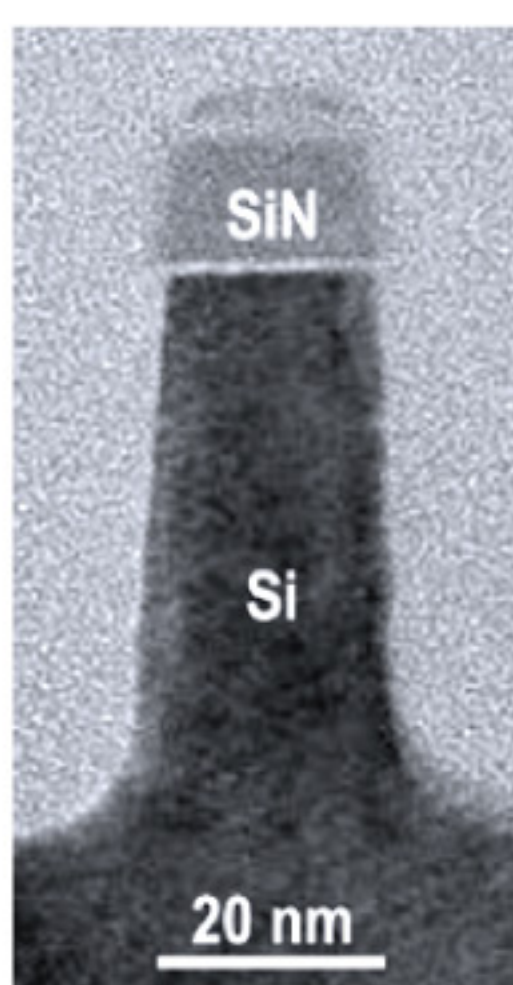
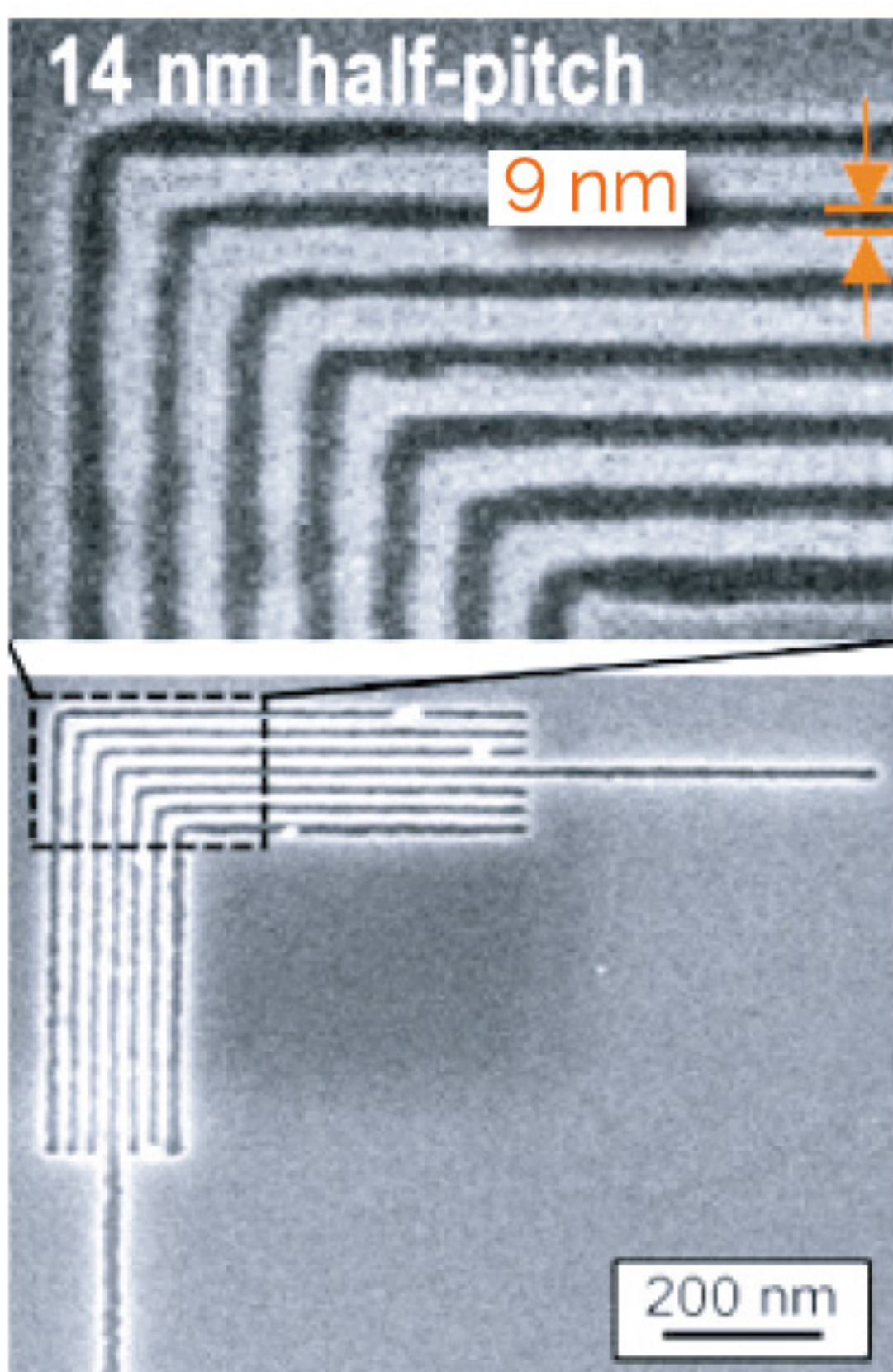


Markerless overlay of metal electrodes on top of a nanowire buried under resist stack. a) Detect nanowire location (green) and draw layout on topography image (pink). b) SEM after lift-off.



- Accurate overlay and stitching achieved by in-situ topography imaging (sub-10 nm accuracy demonstrated)
- Features buried under resist (flakes, wires, etc) are used as natural markers
- Automated correlation stitching of write fields

ULTRA-HIGH RESOLUTION



Silicon fins and trenches etched from PPA resist.

Courtesy of IBM Research and imec

OTHER UNIQUE CAPABILITIES

- Ultra-sharp tips enable ultra-high resolution (< 10 nm half-pitch demonstrated in resist)
- Low damage: No charged particles beam, hence better device performance with sensitive materials
- No proximity effect corrections required
- Material conversion at the nanoscale: direct heat-induced modifications (phase change, chemical reaction, ...) of various materials

NanoFrazor[®] Explore

SYSTEM SPECIFICATIONS

	Thermal Probe Writing	Direct Laser Sublimation
Patterning performance		
Minimum structure size [nm]	15	600
Minimum lines and spaces [half pitch, nm]	25	1000
Grayscale / 3D-resolution (step size in PPA) [nm]	2	-
Writing field size [X μm x Y μm]	60 x 60	60 x 60
Field stitching accuracy (markerless, using in-situ imaging) [nm]	25	600
Overlay accuracy (markerless, using in-situ imaging) [nm]	25	600
Write speed (typical scan speed) [mm/s]	1	5
Write speed (50 nm pixel) [μm ² /min]	1000	100000

Topography imaging performance		
Lateral imaging resolution (feature size) [nm]		10
Vertical resolution (topography sensitivity) [nm]		<0.5
Imaging speed (@ 50 nm resolution) [μm ² /min]		1000

System features	
Substrate sizes	1 x 1 mm ² to 100 x 100 mm ² (150 x 150 mm ² possible with limitations) Thickness: 10 mm with optical access, 15 mm without optical access.
Optical microscope	0.6 μm digital resolution, 2 μm diffraction limit, 1.0 mm x 1.0 mm field of view, autofocus
Laser source and optics	405 nm wavelength CW fiber laser, more than 110 mW output power on sample, 1.2 μm minimum focal spot size
Real-time laser autofocus	Using the distance sensor of the NanoFrazor cantilever
Magnetic cantilever holder	Fast (< 1 min) and accurate tip exchange
Housing	Three-layer acoustic isolation, superior vibration isolation (> 98% @ 10 Hz) PC-controlled temperature and humidity monitoring, gas-flow regulation
Software features	GDS and bitmap import, 0.1 nm address grid, 256 grayscale levels, topography image analysis and drawing for overlay, mix & match between tip and laser writing, fully automated calibration routines, Python scripting

NanoFrazor cantilever features	
Integrated components	Tip heater, topography sensor, electrostatic actuation
Tip geometry	Conical tip with < 10 nm radius and 750 nm length
Tip heater temperature range	25 °C – 1100 °C (< 1 K setpoint resolution)

System dimensions & installation requirements	
Height x width x depth	185 cm x 78 cm x 128 cm
Weight	650 kg
Power input	1 x 110 or 220 V AC, 10 A
Gas input	Compressed air and/or nitrogen with > 4 bar

Other considerations	
Recipe book with detailed descriptions of various processes is available (regularly updated with software).	
Cantilever tips degrade over time (> 50 h patterning possible). Exchange is fast and low cost for tool owners.	
A cleanroom or special laboratory is not required. No vacuum needed.	
Parallel Multi-tip patterning extension (optional add-on for Explore system) is scheduled for beta-testing at end of 2022	

Please note: Specifications depend on individual process conditions and may vary according to equipment configuration.
Write speed depends on exposure area. Design and specifications are subject to change without prior notice.

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